

- *Under forward bias:*
 - *BH reduces to $(V_0 - V_D)$*
 - *Inj that creates current flow $\propto \exp(V_D/V_T)$*
 - Note the *exponential dependence*
 - *Possibility of large injection for large V_D*
 - *Drift component remains more or less same,*
since it is *dependent on the minority carriers*
 - *Current increases exponentially with V_D*
 - *V_D can never equal or exceed V_0*
 - *Thermodynamically untenable situation*

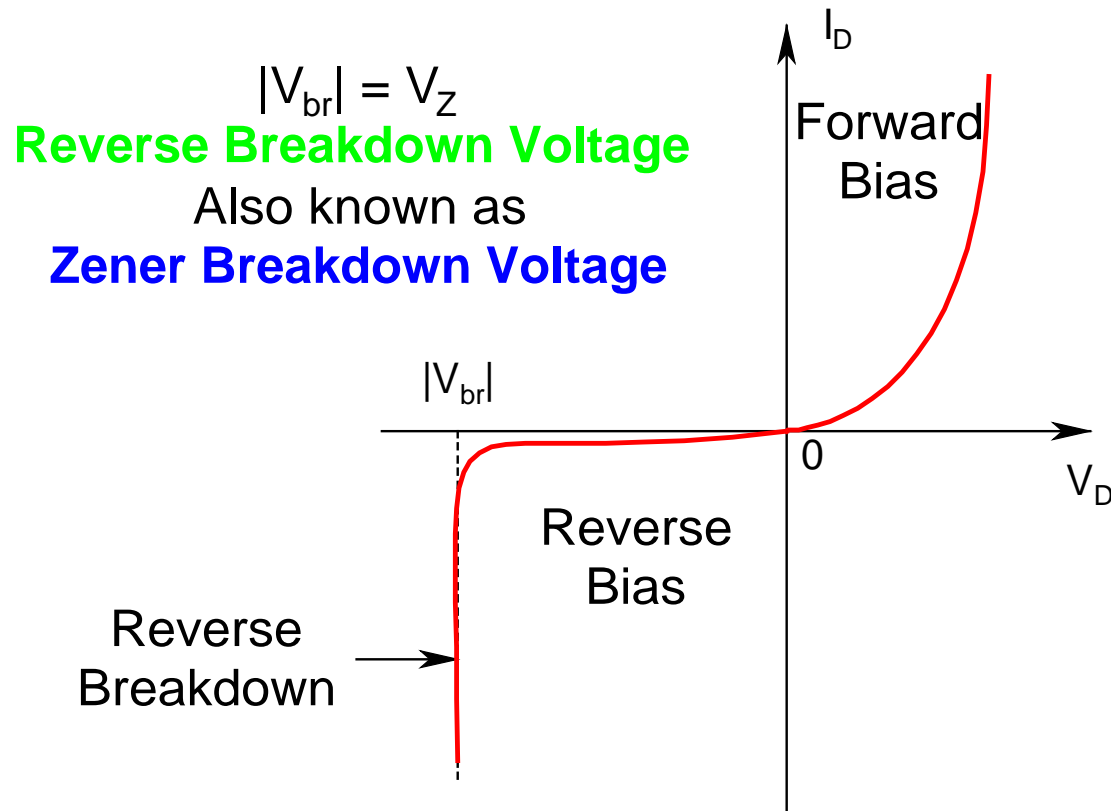
- *Under reverse bias:*
 - *Inj ↓↓ due to negative V_D*
 - *Drift component remains same*
 - Function of *minority carriers* available on the two sides, which is a *constant* (function only of temperature)
 - *Current becomes small and independent of bias*
- In *forward bias*, *both injection components* create *current from p to n*
- In *reverse bias*, *both minority carrier drift components* create *current from n to p*

Current-Voltage Characteristic

- $I_D = I_0[\exp(V_D/V_T) - 1]$
 - I_0 : **Reverse Saturation Current** (\sim nA-fA)
- In **equilibrium**: $V_D = 0 \Rightarrow I_D = 0$
- Under **forward bias**: **V_D positive**
 - I_D **positive** (**flows from p to n**) (\sim mA)
 - For $V_D > 4V_T$ (~ 100 mV at 300 K):
 - $I_D \approx I_0[\exp(V_D/V_T)]$ (**A True Exponent**)

- Under *reverse bias*: V_D *negative*
 - I_D *negative* (*flows from n to p*)
 - For $|V_D| > 4V_T$:
 - $I_D \approx -I_0$ (note the *negative sign*)
 - *Extremely small*, almost negligible
- *Depending on V_D , the ratio of the forward current to the reverse current can range from 5 to 14 orders of magnitude!*
- *Primary applications*:
 - *Rectification* and various types of *waveshaping*

Complete I-V Characteristic



Note that the forward and reverse current scales are not same